



Faculty Profile



1.	Name of the Faculty :	Dr. M. Elangovan
2.	Designation :	Assistant Professor
3.	Department:	Electronics and Communication Engineering
4.	Date of Joining :	25.04.2013
5.	Faculty ID:	AICTE ID: 1-2194277018
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7.	Date of Birth :	01.01.1983
8.	Qualification :	Ph.D
9.	Specialization :	VLSI Design
10.	Professional Experience:	13 years
11.	Research Guidance:	-
12.	Awards and Honors :	-
13.	Sponsored Projects:	-

14.	Patents:	-
15.	Publications (Proof to be Enclosed – First page only)	
	(i) International Referred Journals :	9
	(ii) National Journals:	-
	(iii) International Conferences:	3
	(iv) National Conferences:	-
	(v) Books Published With ISBN Number/ISSN Number:	-
16.	Conferences/Workshops/Seminar/ Short Term Refresher Courses Attended (Proof to be Enclosed)	-
17.	Conferences/Workshops/Seminars Organized	-
18.	Other Contribution (If any)	-

International Journals

1. **Elangovan, M** & Gunavathi, K 2019, High stable and low power 8T CNTFET SRAM cell. Journal of Circuits Systems and Computers, vol. 29, no. 5,
2. **Elangovan, M** & Gunavathi, K 2020, High Stable and Low Power 10T CNTFET SRAM Cell. Journal of Circuits Systems and Computers, vol. 29, no. 10,
3. **M. Elangovan**, D. Karthickeyan, M. Arul Kumar & R. Ranjith 2021, Darlington Based 8T CNTFET SRAM Cells with Low Power and Enhanced Write Stability. Transactions on Electrical and Electronic Materials,
4. **Elangovan, M** 2021, A Novel Darlington-Based 8T CNTFET SRAM Cell for Low Power Applications. Journal of Circuits Systems and Computers.

5. **M. Elangovan, M** & Gunavathi, K 2021, Effect of CNTFET Parameters on Novel High Stable and Low Power: 8T CNTFET SRAM Cell. Transactions on Electrical and Electronic Materials,
6. **Elangovan, M, M. Muthukrishnan**, 2021, A Low-Power and High-Stability 8T SRAM Cell with Diode-Connected Transistors. Journal of Circuits Systems and Computers.
7. **Elangovan, M, M. Muthukrishnan**, 2022, Design of High Stability and Low Power 7T SRAM Cell in 32-NM CNTFET Technology. Journal of Circuits Systems and Computers.
8. **Erfan Abbasian, Elangovan Mani, Morteza Gholipour, Mehrzad Karamimanesh, Mohd Sahid & Adil Zaidi** , 2022A Schmitt-Trigger-Based Low-Voltage 11 T SRAM Cell for Low-Leakage in 7-nm FinFET Technology. Circuits, Systems, and Signal Processing.
9. **Elangovan Mani, Erfan Abbasian, Muthukumaran Gunasegeran, Sobhan Sofimowlood** , 2022, Design of high stability, low power and high speed 12 T SRAM cell in 32-nm CNTFET technology. International Journal of Electronics and Communications.

International Conferences

1. **Elangovan, M** & Gunavathi, K 2018, Stability Analysis of 6T CNTFET SRAM Cell for Single and Multiple CNTs. Fourth International Conference on Devices, Circuits and Systems (ICDCS), India, pp. 63-67.
2. **Elangovan, M** & Gunavathi, K 2018, Power Analysis of 6T CNTFET SRAM Cell for Single and Multiple CNTs. International Symposium on Semiconductor Materials and Devices, India, pp. 64-68.
3. **M. Elangovan**, R. Ranjith, and S. Devika 2021, PDP Analysis of CNTFET Full Adders for Single and Multiple Threshold Voltages, International Conference on Advances in VLSI, Communication, and Signal Processing, India, pp. 439-446.